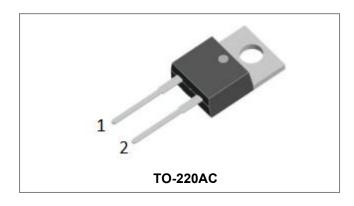






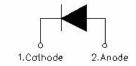
MBR20100 SCHOTTKY RECTIFIER



Features

- 150 °C T_J operation
- Low forward voltage drop
- High purity, high temperature epoxy encapsulation for enhanced
- · mechanical strength and moisture resistance
- High frequency operation
- Guard ring for enhanced ruggedness and long term reliability
- This is a Pb Free Device
- All SMC parts are traceable to the wafer lot
- Additional testing can be offered upon request

Circuit Diagram



Applications

- Switching power supply
- Converters
- Free-Wheeling diodes
- Reverse battery protection

Maximum Ratings:

Characteristics	Symbol	Condition	Max.	Units
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	V _{RRM} V _{RWM} V _R	-	100	V
Average Rectified Forward Current	I _{F (AV)}	50% duty cycle @Tc=125°C, rectangular wave form	20	Α
Peak One Cycle Non-Repetitive Surge Current	I _{FSM}	8.3ms, Half Sine pulse	280	Α

Electrical Characteristics:

Characteristics	Symbol	Condition	Тур.	Max.	Units
Forward Voltage Drop*	V _{F1}	@ 20A, Pulse, T _J = 25 °C	0.80	0.88	V
	V _{F2}	@ 20A, Pulse, T _J = 125 °C	0.70	0.74	V
Reverse Current*	I _{R1}	@V _R = rated V _R , T _J = 25 °C	0.006	1.0	mA
	I _{R2}	@V _R = rated V _R , T _J = 125 °C	0.1	6	mA
Junction Capacitance	Ст	$@V_R = 5V, T_C = 25 °C f_{SIG} = 1MHz$	400	800	pF
Series Inductance	Ls	Measured lead to lead 5 mm from package body	8.0	-	nH
Voltage Rate of Change	dv/dt	-	-	10,000	V/μs

^{*} Pulse width < 300 µs, duty cycle < 2%

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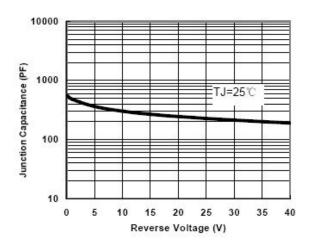




Thermal-Mechanical Specifications:

Characteristics	Symbol	Condition	Specification	Units
Junction Temperature	TJ	-	-55 to +150	°C
Storage Temperature	T _{stg}	-	-55 to +150	°C
Typical Thermal Resistance Junction to Case	R _θ JC	DC operation	3.5	°C/W
Approximate Weight	wt	-	1.6	g
Case Style	TO-220AC			

Ratings and Characteristics Curves



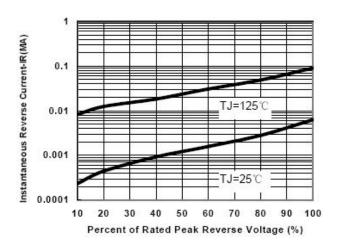


Fig.1-Typical Junction Capacitance

Fig.2-Typical Reverse Characteristics

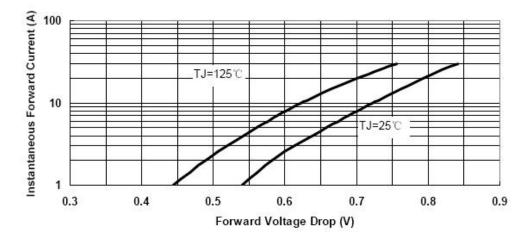


Fig.3-Typical Instantaneous Forward Voltage Characteristics

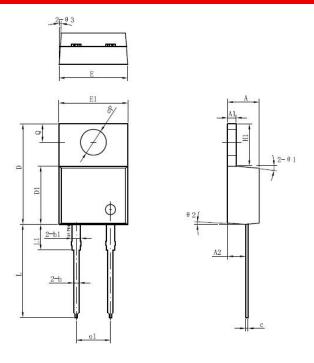
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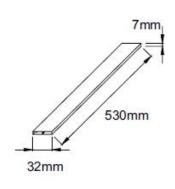


Mechanical Dimensions TO-220AC

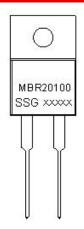


Symbol	Dimensions in millimeters			
	Min.	Typical	Max.	
Α	4.47	4.70	4.85	
A1	1.17	1.27	1.37	
A2	2.52	2.69	2.89	
b	0.71	0.81	0.96	
b1	1.17	1.27	1.37	
С	0.31	0.38	0.61	
D	14.64	14.94	15.24	
D1	8.50	8.07	8.90	
E	10.01	10.16	10.31	
E1	9.98	10.18	10.38	
e1	4.98	5.08	5.18	
H1	6.04	6.24	6.44	
L	13.00	13.86	14.08	
L1	3.56	3.80	3.96	
ФР	3.74	3.84	4.04	
Q	2.54	2.74	2.94	
Θ1		5°		
Θ2		4°		
Θ3		4°		

Tube Specification



Marking Diagram



Where XXXXX is YYWWL

MBR = Device Type 20 = Forward Current (20A) 100 = Reverse Voltage(100V) 5SG = SSG

SSG = SSG YY = Year WW = Week L = Lot Number

Cautions: Molding resin Epoxy resin UL:94V-0

Ordering Information

Device	Package	Shipping	
MBR20100	TO-220AC (Pb-Free)	50 pcs/ tube	

For information on tape and reel specifications, including part orientation and tape sizes, please refer to our tape and reel packaging Specification.

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